# **UTC** UNISONIC TECHNOLOGIES CO., LTD

### UTT6N10Z

## 100V, 6A N-CHANNEL POWER MOSFET

#### DESCRIPTION

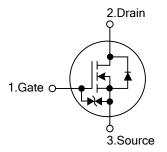
The UTC **UTT6N10Z** is an N-channel enhancement mode Power FET, it uses UTC's advanced technology to provide customers a minimum on-state resistance, high switching speed and ultra low gate charge.

The UTC **UTT6N10Z** is usually used in DC-DC Conversion.

#### FEATURES

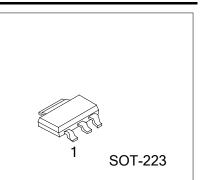
- \*  $R_{DS(on)}$  =80m $\Omega$  @V<sub>GS</sub> = 10 V,I<sub>D</sub>=6A
- \* High Switching Speed
- \* Low Crss (Typically 3.1pF)
- \* Low Gate Charge(Typically 4.3nC)





#### ORDERING INFORMATION

Ordering Number		Deelvere	Pin Assignment			Decking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTT6N10ZL-AA3-R	UTT6N10ZG-AA3-R	SOT-223	G	D	S	Tape Reel	
Note: Pin Assignment: G: Gate D: Drain S: Source							
UTT6N10ZL-AA3-R (1)Packing Type (2)Package Type (3)Lead Free		(1) R: Tape Reel (2) AA3: SOT-223 (3) L: Lead Free, G: Halogen Free					



**Power MOSFET** 

#### ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>c</sub>=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V <sub>DSS</sub>	100	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Drain Current	Continuous	ID	6	А
	Pulsed	I <sub>DM</sub>	24	А
Single Pulsed Avalanche Energy (Note 3)		E <sub>AS</sub>	12	mJ
Power Dissipation	T <sub>A</sub> =25°C (Note 1)	PD	2.2	W
Junction Temperature		$T_J$	150	°C
Storage Temperature Range		T <sub>STG</sub>	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient (Note 1)	θ <sub>JA</sub>	55	°C/W	
Junction to Case	θ <sub>JC</sub>	12	°C/W	

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μΑ, V <sub>GS</sub> =0V				V	
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V			1	μA	
Cata Source Leakage Current Forward		V <sub>GS</sub> =+20V, V <sub>DS</sub> =0V			+10	μA	
Gate-Source Leakage Current Reverse	I <sub>GSS</sub>	V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V			-10	μA	
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250µA			2.2	V	
Statia Duain Course On State Desistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =6A		80	108	mΩ	
Static Drain-Source On-State Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A		100	153	mΩ	
DYNAMIC PARAMETERS							
Input Capacitance	CISS	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1.0MHz		234	315	рF	
Output Capacitance	Coss			46	65	рF	
Reverse Transfer Capacitance	C <sub>RSS</sub>			3.1	5	рF	
SWITCHING PARAMETERS							
Total Gate Charge	$Q_{G}$	V <sub>GS</sub> =10V, V <sub>DD</sub> =25V, I <sub>D</sub> =6A		4.3	7	nC	
Gate to Source Charge	$Q_{GS}$	V <sub>DD</sub> =50V, I <sub>D</sub> =6A		0.7		nC	
Gate to Drain Charge	$Q_{GD}$	V <sub>DD</sub> =50V, I <sub>D</sub> =6A		0.9		nC	
Turn-ON Delay Time	t <sub>D(ON)</sub>			3.8	10	ns	
Rise Time	t <sub>R</sub>	V <sub>DD</sub> =50V, I <sub>D</sub> =6A, V <sub>GS</sub> =10V, R <sub>GEN</sub> =6Ω		1.3	10	ns	
Turn-OFF Delay Time	t <sub>D(OFF)</sub>			10	20	ns	
Fall-Time	t <sub>F</sub>			1.5	10	ns	
SOURCE- DRAIN DIODE RATINGS AND	CHARACTERI	STICS					
ssDrain-Source Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =6A, V <sub>GS</sub> =0V (Note 2) 0		0.86	1.3	V	
Maximum Body-Diode Continuous Current	ls				6	А	
Source Current Pulsed	I <sub>SM</sub>				24	А	

Notes: 1.  $\theta_{JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.

 $\theta_{JC}$  is guaranteed by design while  $\theta_{JA}$  is determined by the user's board deign.

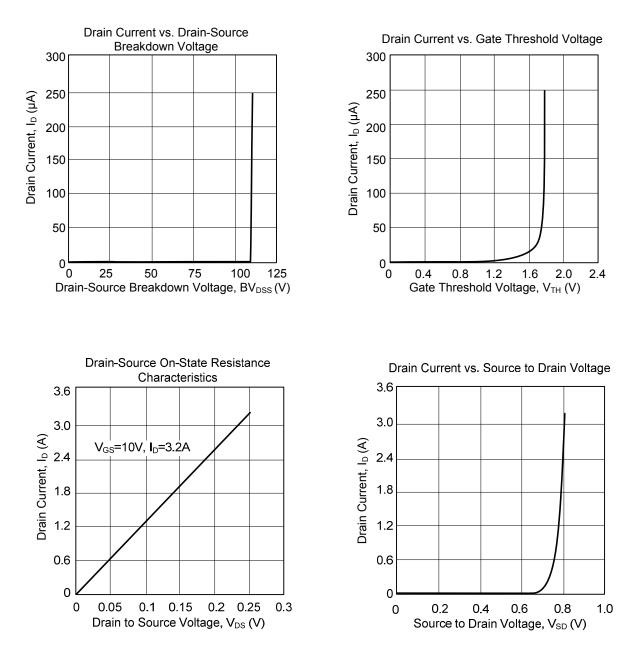
2. Pulse Test: Pulse width  $\leq$  300µs, Duty cycle  $\leq$  2%

3. Starting  $T_J$  = 25°C, L =11mH, I<sub>AS</sub> =6A, V<sub>DD</sub> = 90V, V<sub>GS</sub>=10V.



## UTT6N10Z

#### TYPICAL CHARACTERISTICS



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